

# 30V N-Channel NexFET™ Power MOSFET

 Check for Samples: [CSD17312Q5](#)

## FEATURES

- Optimized for 5V Gate Drive
- Ultra Low  $Q_g$  and  $Q_{gd}$
- Low Thermal Resistance
- Avalanche Rated
- Pb Free Terminal Plating
- RoHS Compliant
- Halogen Free
- SON 5-mm x 6-mm Plastic Package

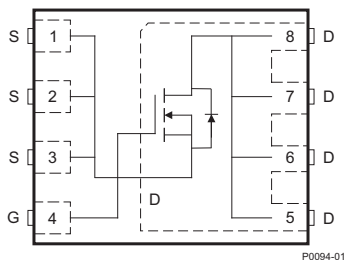
## APPLICATIONS

- Notebook Point-of-Load
- Point-of-Load Synchronous Buck in Networking, Telecom and Computing Systems

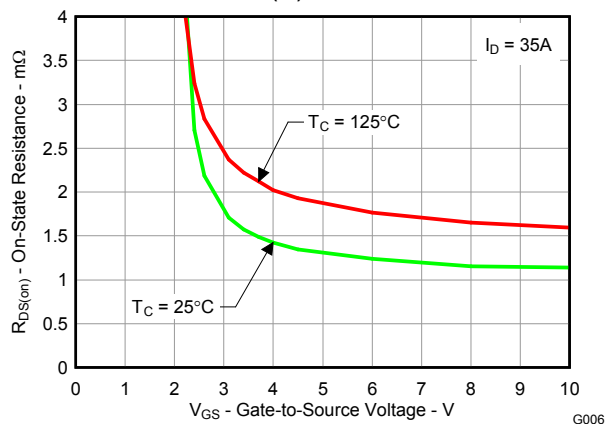
## DESCRIPTION

The NexFET™ power MOSFET has been designed to minimize losses in power conversion applications and optimized for 5V gate drive applications.

Top View



P0094-01

 $R_{DS(on)}$  vs  $V_{GS}$ 


G006

## PRODUCT SUMMARY

$V_{DS}$	Drain to Source Voltage	30	V
$Q_g$	Gate Charge Total (4.5V)	28	nC
$Q_{gd}$	Gate Charge Gate to Drain	6	nC
$R_{DS(on)}$	Drain to Source On Resistance	$V_{GS} = 3V$	1.8 mΩ
		$V_{GS} = 4.5V$	1.4 mΩ
		$V_{GS} = 8V$	1.2 mΩ
$V_{GS(th)}$	Threshold Voltage	1.1	V

## ORDERING INFORMATION

Device	Package	Media	Qty	Ship
CSD17312Q5	SON 5-mm x 6-mm Plastic Package	13-Inch Reel	2500	Tape and Reel

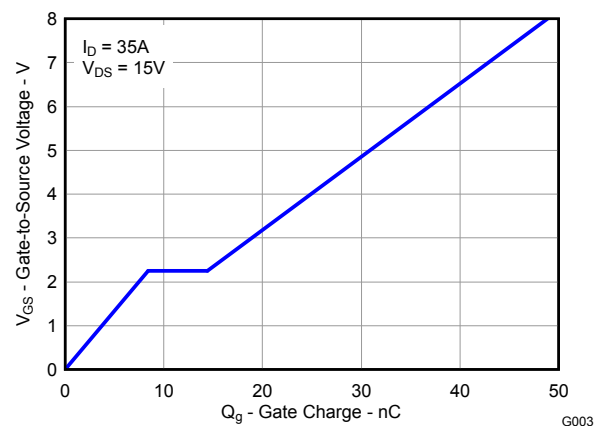
## ABSOLUTE MAXIMUM RATINGS

$T_A = 25^\circ\text{C}$ unless otherwise stated		VALUE	UNIT
$V_{DS}$	Drain to Source Voltage	30	V
$V_{GS}$	Gate to Source Voltage	+10 / -8	V
$I_D$	Continuous Drain Current, $T_C = 25^\circ\text{C}$	100	A
	Continuous Drain Current <sup>(1)</sup>	38	A
$I_{DM}$	Pulsed Drain Current, $T_A = 25^\circ\text{C}$ <sup>(2)</sup>	200	A
$P_D$	Power Dissipation <sup>(1)</sup>	3.2	W
$T_J, T_{STG}$	Operating Junction and Storage Temperature Range	-55 to 150	$^\circ\text{C}$
$E_{AS}$	Avalanche Energy, Single Pulse $I_D = 130A, L = 0.1mH, R_G = 25\Omega$	845	mJ

(1) Typical  $R_{\theta JA} = 39^\circ\text{C}/\text{W}$  when mounted on a 1-inch<sup>2</sup> (6.45-cm<sup>2</sup>), 2-oz. (0.071-mm thick) Cu pad on a 0.06-inch (1.52-mm) thick FR4 PCB.

(2) Pulse duration  $\leq 300\mu\text{s}$ , duty cycle  $\leq 2\%$

GATE CHARGE



G003



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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

## ELECTRICAL CHARACTERISTICS

(T<sub>A</sub> = 25°C unless otherwise stated)

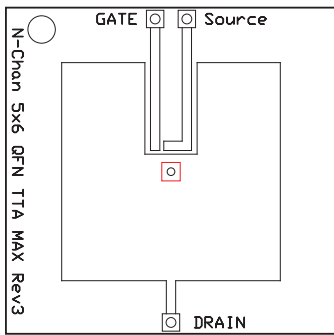
PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
<b>Static Characteristics</b>						
BV <sub>DSS</sub>	Drain to Source Voltage	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA	30			V
I <sub>DSS</sub>	Drain to Source Leakage Current	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 24V			1	μA
I <sub>GSS</sub>	Gate to Source Leakage Current	V <sub>DS</sub> = 0V, V <sub>GS</sub> = +10/-8V			100	nA
V <sub>GS(th)</sub>	Gate to Source Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	0.9	1.1	1.5	V
R <sub>DS(on)</sub>	Drain to Source On Resistance	V <sub>GS</sub> = 3V, I <sub>D</sub> = 35A		1.8	2.4	mΩ
		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 35A		1.4	1.7	mΩ
		V <sub>GS</sub> = 8V, I <sub>D</sub> = 35A		1.2	1.5	mΩ
g <sub>fs</sub>	Transconductance	V <sub>DS</sub> = 15V, I <sub>D</sub> = 35A		200		S
<b>Dynamic Characteristics</b>						
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 15V, f = 1MHz	4030	5240		pF
C <sub>oss</sub>	Output Capacitance		2220	2890		pF
C <sub>rss</sub>	Reverse Transfer Capacitance		93	120		pF
R <sub>G</sub>	Series Gate Resistance		1.1	2.2		Ω
Q <sub>g</sub>	Gate Charge Total (4.5V)	V <sub>DS</sub> = 15V, I <sub>DS</sub> = 35A	28	36		nC
Q <sub>gd</sub>	Gate Charge Gate to Drain		6			nC
Q <sub>gs</sub>	Gate Charge Gate to Source		8.4			nC
Q <sub>g(th)</sub>	Gate Charge at V <sub>th</sub>		4.4			nC
Q <sub>oss</sub>	Output Charge	V <sub>DS</sub> = 14.8V, V <sub>GS</sub> = 0V	57			nC
t <sub>d(on)</sub>	Turn On Delay Time	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 4.5V, I <sub>DS</sub> = 35A, R <sub>G</sub> = 2Ω	9.5			ns
t <sub>r</sub>	Rise Time		27			ns
t <sub>d(off)</sub>	Turn Off Delay Time		35			ns
t <sub>f</sub>	Fall Time		23			ns
<b>Diode Characteristics</b>						
V <sub>SD</sub>	Diode Forward Voltage	I <sub>SD</sub> = 35A, V <sub>GS</sub> = 0V	0.8	1		V
Q <sub>rr</sub>	Reverse Recovery Charge	V <sub>DD</sub> = 14.8V, I <sub>F</sub> = 35A, di/dt = 300A/μs	88			nC
t <sub>rr</sub>	Reverse Recovery Time		43			ns

## THERMAL CHARACTERISTICS

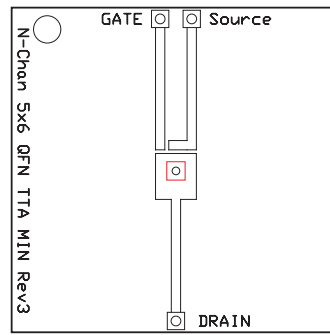
(T<sub>A</sub> = 25°C unless otherwise stated)

PARAMETER		MIN	TYP	MAX	UNIT
R <sub>θJC</sub>	Thermal Resistance Junction to Case <sup>(1)</sup>			1	°C/W
R <sub>θJA</sub>	Thermal Resistance Junction to Ambient <sup>(1)(2)</sup>			49	°C/W

- (1) R<sub>θJC</sub> is determined with the device mounted on a 1-inch<sup>2</sup> (6.45-cm<sup>2</sup>), 2-oz. (0.071-mm thick) Cu pad on a 1.5-inch × 1.5-inch (3.81-cm × 3.81-cm), 0.06-inch (1.52-mm) thick FR4 PCB. R<sub>θJC</sub> is specified by design, whereas R<sub>θJA</sub> is determined by the user's board design.
- (2) Device mounted on FR4 material with 1-inch<sup>2</sup> (6.45-cm<sup>2</sup>), 2-oz. (0.071-mm thick) Cu.



Max  $R_{\theta JA} = 49^{\circ}\text{C/W}$   
when mounted on  
1 inch<sup>2</sup> (6.45 cm<sup>2</sup>) of  
2-oz. (0.071-mm thick)  
Cu.



Max  $R_{\theta JA} = 119^{\circ}\text{C/W}$   
when mounted on a  
minimum pad area of  
2-oz. (0.071-mm thick)  
Cu.

### TYPICAL MOSFET CHARACTERISTICS

( $T_A = 25^{\circ}\text{C}$  unless otherwise stated)

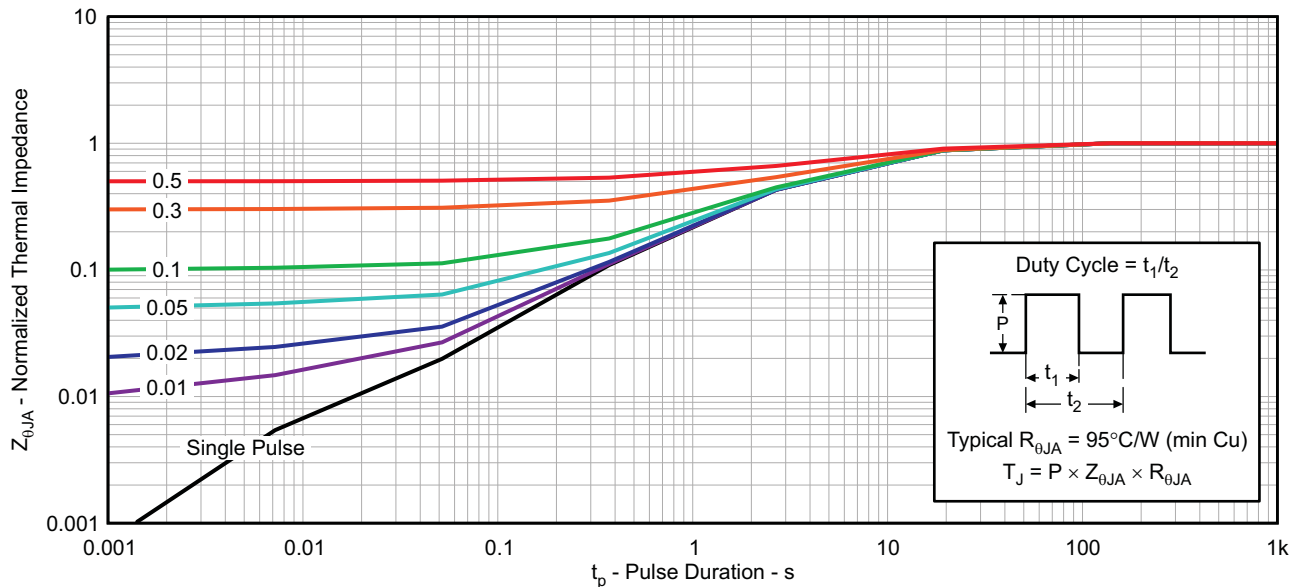
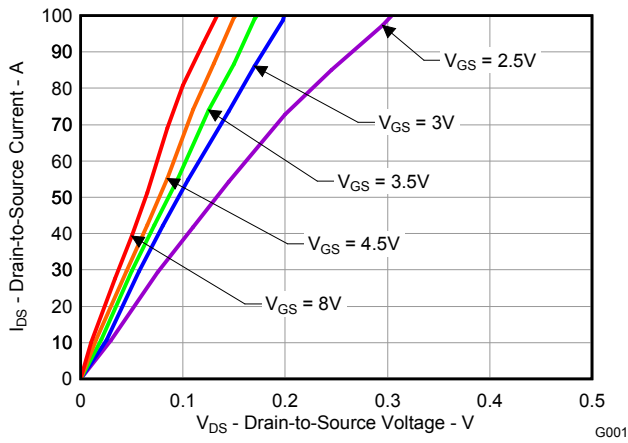


Figure 1. Transient Thermal Impedance

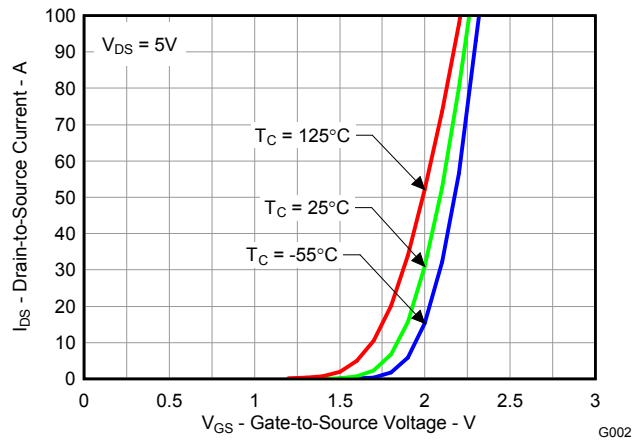
G012

**TYPICAL MOSFET CHARACTERISTICS (continued)**

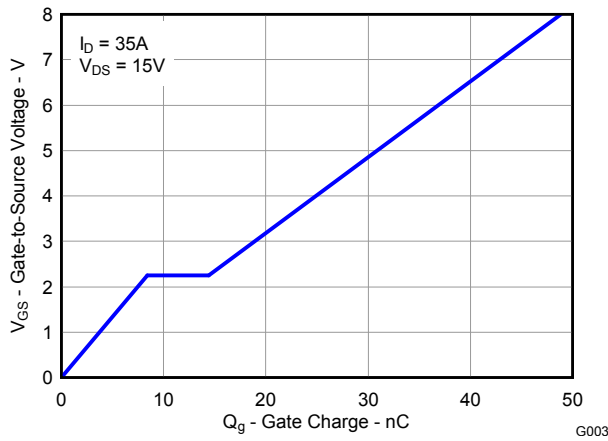
( $T_A = 25^\circ\text{C}$  unless otherwise stated)



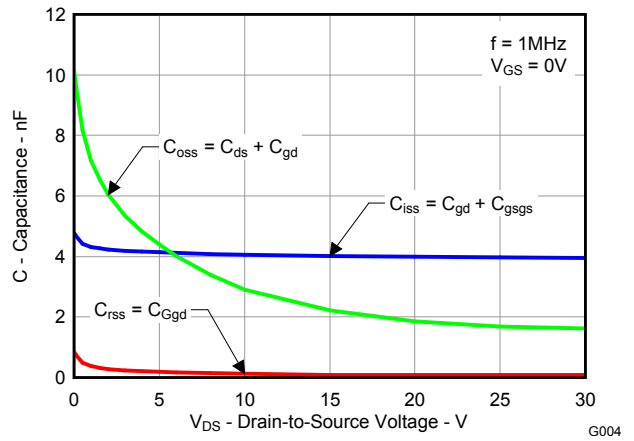
**Figure 2. Saturation Characteristics**



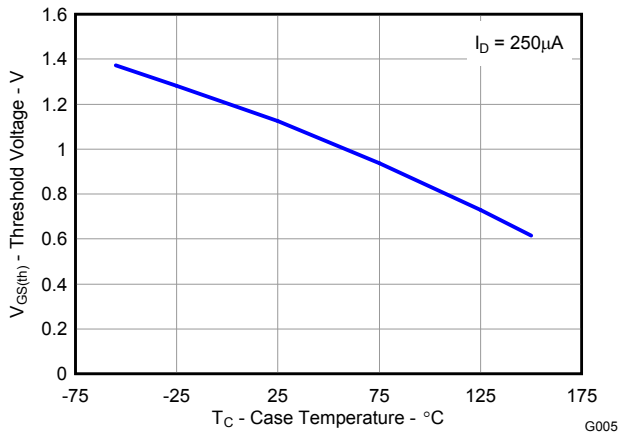
**Figure 3. Transfer Characteristics**



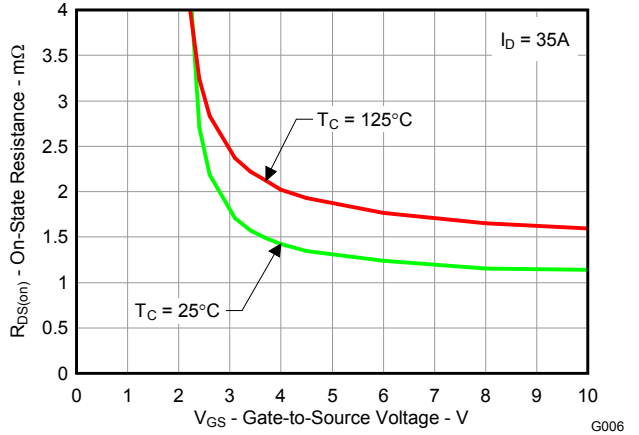
**Figure 4. Gate Charge**



**Figure 5. Capacitance**



**Figure 6. Threshold Voltage vs. Temperature**



**Figure 7. On-State Resistance vs. Gate-to-Source Voltage**

TYPICAL MOSFET CHARACTERISTICS (continued)

( $T_A = 25^\circ\text{C}$  unless otherwise stated)

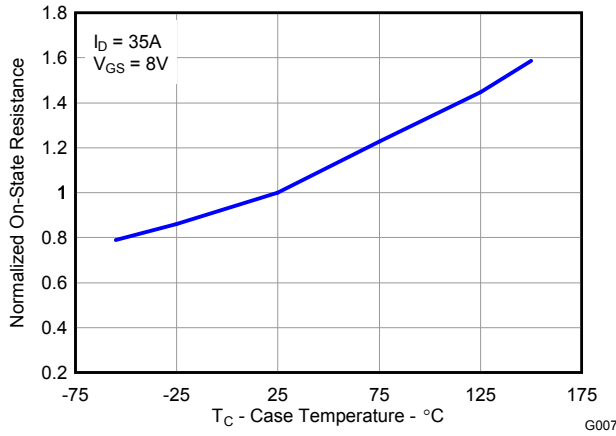


Figure 8. Normalized On-State Resistance vs. Temperature

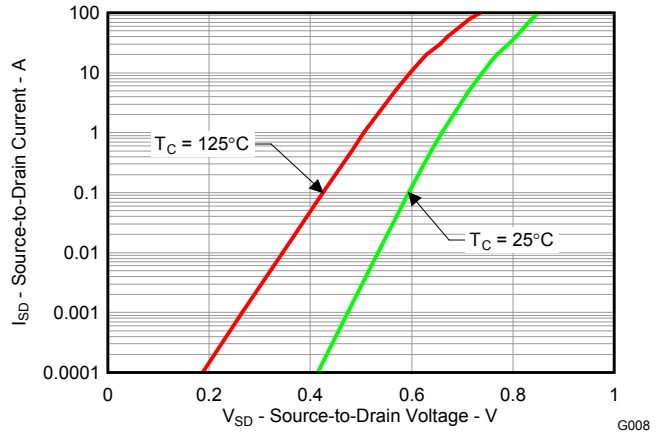


Figure 9. Typical Diode Forward Voltage

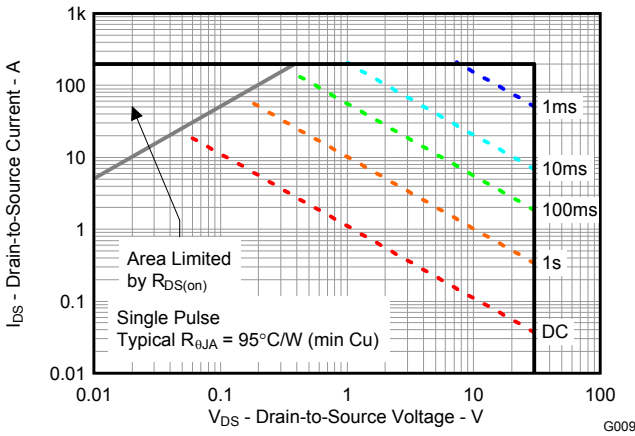


Figure 10. Maximum Safe Operating Area

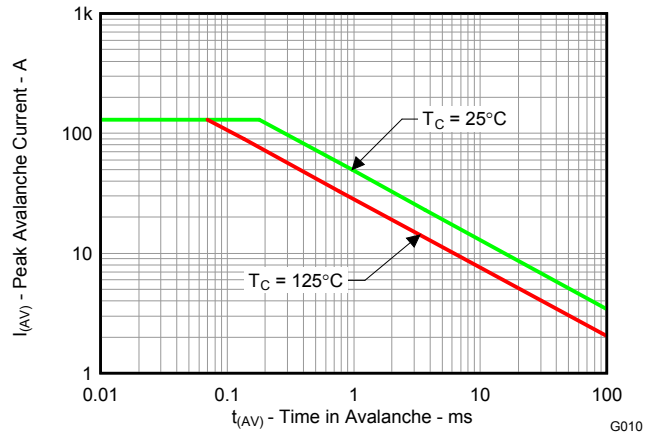


Figure 11. Single Pulse Unclamped Inductive Switching

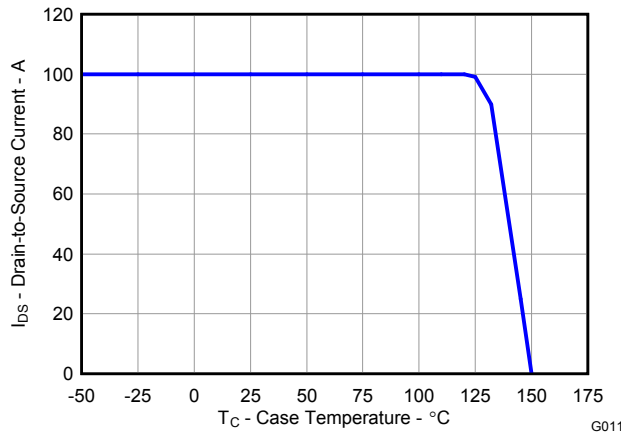
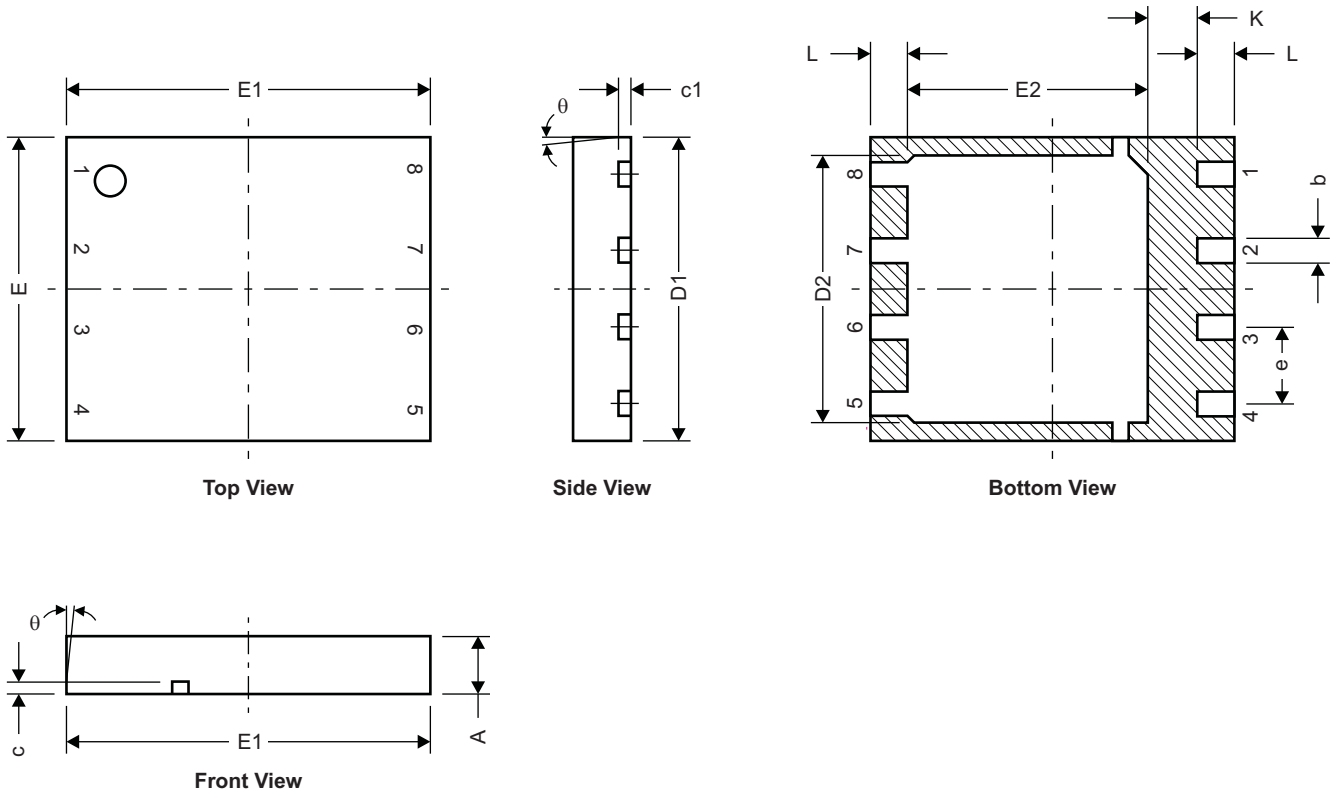


Figure 12. Maximum Drain Current vs. Temperature

**MECHANICAL DATA**

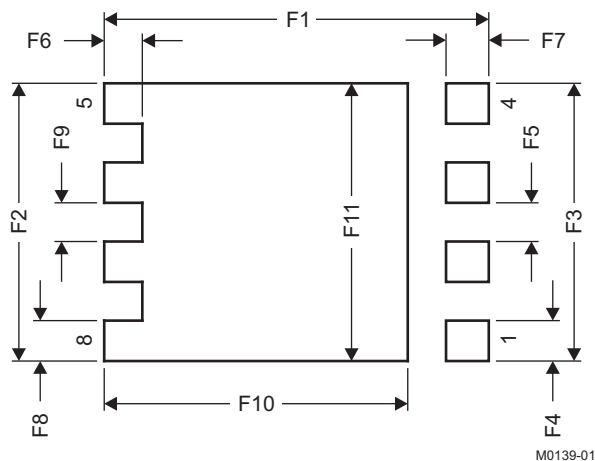
**Q5 Package Dimensions**



M0140-01

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.950	1.050	0.037	0.039
b	0.360	0.460	0.014	0.018
c	0.150	0.250	0.006	0.010
c1	0.150	0.250	0.006	0.010
D1	4.900	5.100	0.193	0.201
D2	4.320	4.520	0.170	0.178
E	4.900	5.100	0.193	0.201
E1	5.900	6.100	0.232	0.240
E2	3.920	4.12	0.154	0.162
e	1.27 TYP		0.050	
K	0.760		0.030	
L	0.510	0.710	0.020	0.028
$\theta$	0.00			

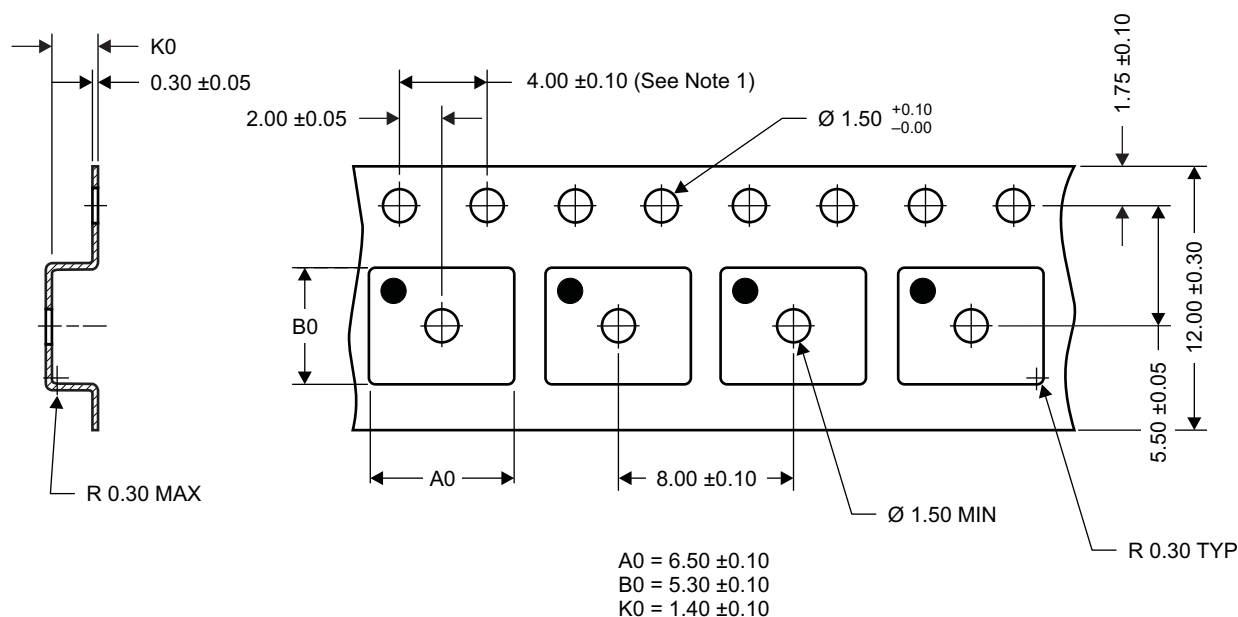
### Recommended PCB Pattern



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
F1	6.205	6.305	0.244	0.248
F2	4.460	4.560	0.176	0.180
F3	4.460	4.560	0.176	0.180
F4	0.650	0.700	0.026	0.028
F5	0.620	0.670	0.024	0.026
F6	0.630	0.680	0.025	0.027
F7	0.700	0.800	0.028	0.031
F8	0.650	0.700	0.026	0.028
F9	0.620	0.670	0.024	0.026
F10	4.900	5.000	0.193	0.197
F11	4.460	4.560	0.176	0.180

For recommended circuit layout for PCB designs, see application note [SLPA005 – Reducing Ringing Through PCB Layout Techniques](#).

### Q5 Tape and Reel Information



- Notes:
1. 10-sprocket hole-pitch cumulative tolerance  $\pm 0.2$
  2. Camber not to exceed 1mm in 100mm, noncumulative over 250mm
  3. Material: black static-dissipative polystyrene
  4. All dimensions are in mm, unless otherwise specified.
  5. Thickness:  $0.30 \pm 0.05$ mm
  6. MSL1 260°C (IR and convection) PbF reflow compatible

M0138-01

### Package Marking Information

**Location**

**1st Line**

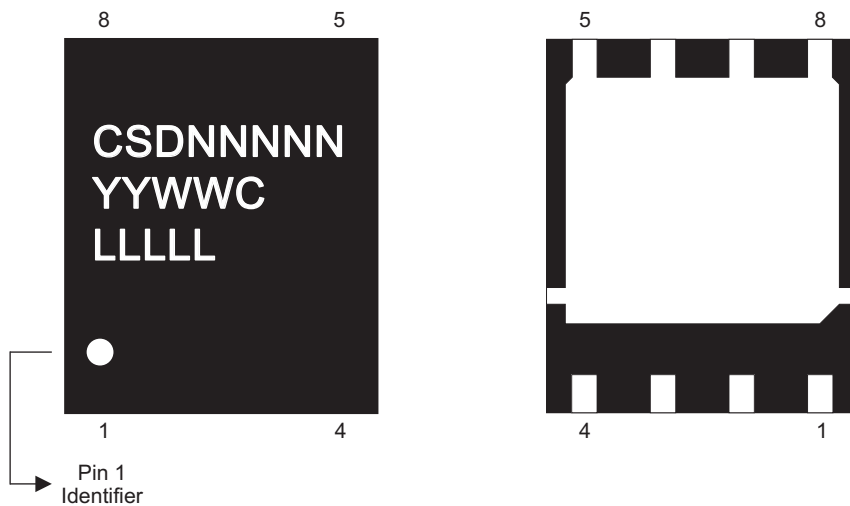
CSD = Fixed Characters  
 NNNNN = Product Code

**2nd Line (Date Code)**

YY = Last 2 digits of the Year  
 WW = 2-digit Work Week  
 C = Country of Origin  
 > Philippines = P  
 > Taiwan = T  
 > China = C

**3rd Line**

LLLL = Last 5 digits of the Wafer Lot #



M0141-01



**PACKAGING INFORMATION**

Orderable Device	Status <sup>(1)</sup>	Package Type	Package Drawing	Pins	Package Qty	Eco Plan <sup>(2)</sup>	Lead/ Ball Finish	MSL Peak Temp <sup>(3)</sup>	Samples (Requires Login)
CSD17312Q5	ACTIVE	SON	DQH	8	2500	Pb-Free (RoHS Exempt)	Call TI	Level-1-260C-UNLIM	<a href="#">Purchase Samples</a>

<sup>(1)</sup> The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

<sup>(2)</sup> Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check <http://www.ti.com/productcontent> for the latest availability information and additional product content details.

**TBD:** The Pb-Free/Green conversion plan has not been defined.

**Pb-Free (RoHS):** TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

**Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

**Green (RoHS & no Sb/Br):** TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

<sup>(3)</sup> MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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Data Converters	<a href="http://dataconverter.ti.com">dataconverter.ti.com</a>	Automotive	<a href="http://www.ti.com/automotive">www.ti.com/automotive</a>
DLP® Products	<a href="http://www.dlp.com">www.dlp.com</a>	Communications and Telecom	<a href="http://www.ti.com/communications">www.ti.com/communications</a>
DSP	<a href="http://dsp.ti.com">dsp.ti.com</a>	Computers and Peripherals	<a href="http://www.ti.com/computers">www.ti.com/computers</a>
Clocks and Timers	<a href="http://www.ti.com/clocks">www.ti.com/clocks</a>	Consumer Electronics	<a href="http://www.ti.com/consumer-apps">www.ti.com/consumer-apps</a>
Interface	<a href="http://interface.ti.com">interface.ti.com</a>	Energy	<a href="http://www.ti.com/energy">www.ti.com/energy</a>
Logic	<a href="http://logic.ti.com">logic.ti.com</a>	Industrial	<a href="http://www.ti.com/industrial">www.ti.com/industrial</a>
Power Mgmt	<a href="http://power.ti.com">power.ti.com</a>	Medical	<a href="http://www.ti.com/medical">www.ti.com/medical</a>
Microcontrollers	<a href="http://microcontroller.ti.com">microcontroller.ti.com</a>	Security	<a href="http://www.ti.com/security">www.ti.com/security</a>
RFID	<a href="http://www.ti-rfid.com">www.ti-rfid.com</a>	Space, Avionics & Defense	<a href="http://www.ti.com/space-avionics-defense">www.ti.com/space-avionics-defense</a>
RF/IF and ZigBee® Solutions	<a href="http://www.ti.com/lprf">www.ti.com/lprf</a>	Video and Imaging	<a href="http://www.ti.com/video">www.ti.com/video</a>
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